











SN74LVC2G17

SCES381N - JANUARY 2002 - REVISED JANUARY 2015

SN74LVC2G17 Dual Schmitt-Trigger Buffer

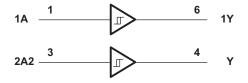
Features

- Schmitt-Trigger inputs provide hysteresis
- Available in the Texas Instruments NanoFree™ Package
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 5.4 ns at 3.3 V
- Low Power Consumption, 10-µA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) $< 0.8 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) $> 2 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Ioff Supports Live Insertion, Partial-Power-Down Mode Operation and Back-Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model
 - 1000-V Charged-Device Model

Applications

- **AV Receivers**
- Audio Docks: Portable
- Blu-ray Players and Home Theater
- MP3 Players/Recorders
- Personal Digital Assistants (PDAs)
- Power: Telecom/Server AC/DC Supply: Single Controller: Analog and Digital
- Solid State Drives (SSDs): Client and Enterprise
- TVs: LCD/Digital and High-Definition (HDTVs)
- Tablets: Enterprise
- Video Analytics: Server
- Wireless Headsets, Keyboards, and Mice

Simplified Schematic



3 Description

This dual Schmitt-Trigger buffer is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G17 device contains two buffers and performs the Boolean function Y = A. The device functions as two independent buffers, but because of Schmitt action, it may have different input threshold levels for positive-going (V_{T+}) and negative-going $(V_{T_{-}})$ signals.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Device Information⁽¹⁾

PART NUMBER	PACKAGE (PIN)	BODY SIZE					
SN74LVC2G17	SOT-23 (6)	2.90 mm x 1.60 mm					
	SC70 (6)	2.00 mm x 1.25 mm					
	SON (6)	1.45 mm × 1.00 mm					
	SON (6)	1.00 mm × 1.00 mm					
	DSBGA (6)	1.41 mm × 0.91 mm					

(1) For all available packages, see the orderable addendum at the end of the data sheet.



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5 Revision History

Changes from Revision M (November 2013) to Revision N

Page

Added Applications, Device Information table, Pin Functions table, ESD Ratings table, Thermal Information table,
Typical Characteristics, Feature Description section, Device Functional Modes, Application and Implementation
section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and
Mechanical, Packaging, and Orderable Information section.

Changes from Revision L (September 2013) to Revision M

Page

Changes from Revision K (July 2012) to Revision L

Page

Updated document to new TI data sheet format.
 Added ESD warning.

Changes from Revision J (June 2012) to Revision K

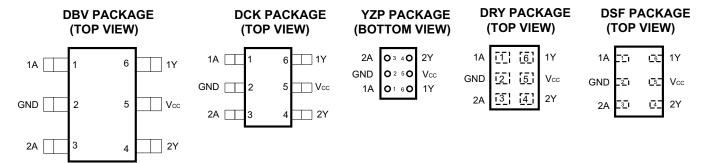
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6 Pin Configuration and Functions



Pin Functions

PI	IN	TYPE	DESCRIPTION
NAME	NO.	ITPE	DESCRIPTION
1A	1	I	Input 1
1Y	6	0	Output 1
2A	3	I	Input 2
2Y	4	0	Output 2
GND	2	_	Ground
V _{CC}	5	_	Power Pin



7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	6.5	V
VI	Input voltage range ⁽²⁾		-0.5	6.5	V
Vo	Voltage range applied to any output in the hig	h-impedance or power-off state ⁽²⁾	-0.5	6.5	V
Vo	Voltage range applied to any output in the hig	h or low state (2)(3)	-0.5	$V_{CC} + 0.5$	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
T_{J}	Junction temperature under bias			150	°C
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

		VALUE	UNIT
	Human-Body Model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (2)	2000	V
V _{ESD} ⁽¹⁾	Charged-Device Model (CDM), per JEDEC specification JESD22-C101, all pins (3)	1000	V

⁽¹⁾ Electrostatic discharge (ESD) to measure device sensitivity and immunity to damage caused by assembly line electrostatic discharges in to the device.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	1.65	5.5	V
V_{I}	Input voltage	·	0	5.5	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 1.65 V		-4	
		$V_{CC} = 2.3 \text{ V}$		-8	
I_{OH}	High-level output current	V - 3 V		-16	mA
		$V_{CC} = 3 V$		-24	
		$V_{CC} = 4.5 \text{ V}$		-32	
		V _{CC} = 1.65 V		4	
		$V_{CC} = 2.3 \text{ V}$		8	
I_{OL}	Low-level output current	V 2.V		16	mA
		$V_{CC} = 3 V$		24	
		$V_{CC} = 4.5 \text{ V}$		32	
T _A	Operating free-air temperature		-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

⁽²⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

³⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LVC2G17						ı
		DBV	DCK	YZP	DRY	DSF	UNIT	
			6 PINS					
$R_{\theta JA}$	Junction-to-ambient thermal resistance (2)	165	259	123	234	300	°C/W	1

For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953. The package thermal impedance is calculated in accordance with JESD 51-7.

7.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

		.,	-40°	C to 85°C	-40°C	to 125°C		
PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP ⁽¹⁾ MAX	MIN	TYP ⁽¹⁾ MAX	UNIT	
		1.65 V	0.7	1.4	0.7	1.4		
V_{T+}		2.3 V	1.0	1.7	1.0	1.7		
Positive-going input threshold		3 V	1.3	2.0	1.3	2.0	V	
voltage		4.5 V	1.9	3.1	1.9	3.1		
		5.5 V	2.2	3.7	2.2	3.7		
		1.65 V	0.3	0.7	0.3	0.7		
V_{T-}		2.3 V	0.4	1	0.4	1.0		
Negative-going input threshold		3 V	0.8	1.3	0.8	1.3	V	
voltage		4.5 V	1.1	2	1.1	2.0		
		5.5 V	1.4	2.5	1.4	2.5		
		1.65 V	0.3	0.8	0.3	0.8		
ΔV_{T}		2.3 V	0.4	0.9	0.35	0.9		
Hysteresis		3 V	0.4	1.1	0.4	1.1	V	
$(V_{T+}^{}-V_{T-}^{})$		4.5 V	0.6	1.3	0.6	1.3		
		5.5 V	0.7	1.4	0.7	1.4		
	$I_{OH} = -100 \mu A$	1.65 V to 5.5 V	V _{CC} - 0.1		$V_{CC} - 0.1$			
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2		1.2			
V_{OH}	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9		1.9		V	
VOH	$I_{OH} = -16 \text{ mA}$	3 V	2.4		2.4		V	
	$I_{OH} = -24 \text{ mA}$	3 V	2.3		2.3			
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8		3.8			
	I _{OL} = 100 μA	1.65 V to 5.5 V		0.1		0.1		
	I _{OL} = 4 mA	1.65 V		0.45		0.45		
V_{OL}	I _{OL} = 8 mA	2.3 V		0.3		0.3	V	
VOL	I _{OL} = 16 mA	3 V		0.4		0.4	V	
	I _{OL} = 24 mA	3 V		0.55		0.55		
	I _{OL} = 32 mA	4.5 V		0.55		0.55		
I _I A inpu	t V _I = 5.5 V or GND	0 to 5.5 V		±5		±5	μΑ	
I _{off}	V_I or $V_O = 5.5 \text{ V}$	0		±10		±10	μΑ	
I _{CC}	$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V		10		10	μΑ	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 5.5 V		500		500	μΑ	
C_{i}	$V_I = V_{CC}$ or GND	3.3 V		4		4	pF	

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.



7.6 Switching Characteristics, -40°C to 85°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

						−40°C t	o 85°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1 ± 0.15		V _{CC} = 2 ± 0.2		V _{CC} = 3 ± 0.3		V _{CC} = ± 0.5		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	3.9	9.3	1.9	5.7	2.2	5.4	1.5	4.3	ns

7.7 Switching Characteristics, -40°C to 125°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

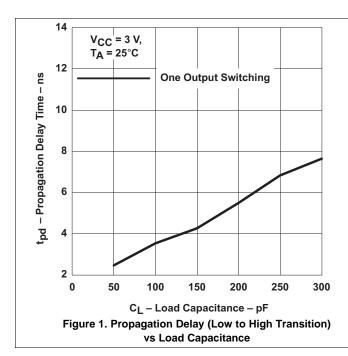
						-40°C to	o 125°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ' ± 0.1		V _{CC} = 2 ± 0.2		V _{CC} = 3 ± 0.3		V _{CC} = ± 0.5		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	3.9	9.8	1.9	6.2	2.2	5.9	1.5	4.8	ns

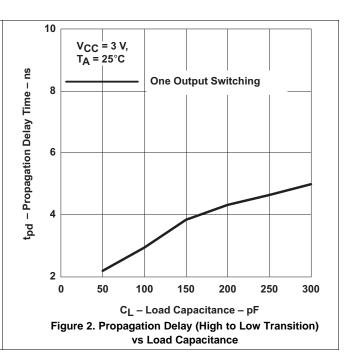
7.8 Operating Characteristics

 $T_A = 25^{\circ}C$

PARAMETER TEST CONDIT		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT	
	FARAINETER	TEST CONDITIONS	TYP	TYP	TYP	TYP	UNII	
C	Power dissipation capacitance	f = 10 MHz	17	18	19	21	pF	

7.9 Typical Characteristics



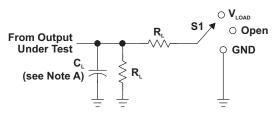


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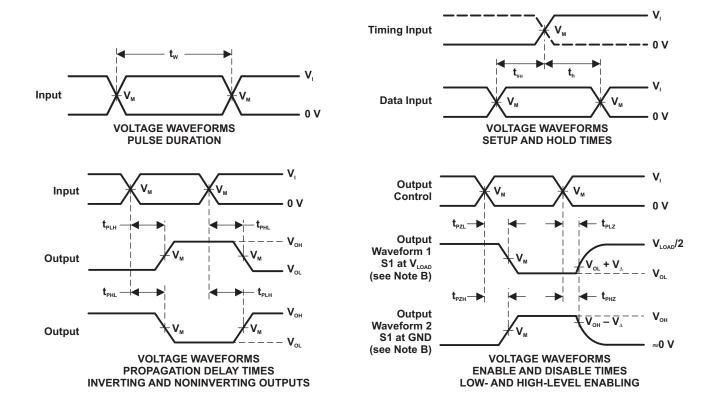
8 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

L	OA	D	CI	R	CI	UI	т

.,	INPUTS			.,			.,	
V _{cc}	V _i	t,/t,	V _M	V _{LOAD}	C _L	R _∟	V _A	
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V	
$2.5~V~\pm~0.2~V$	V_{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V	
$3.3~V~\pm~0.3~V$	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V	
5 V ± 0.5 V	V_{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V	



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{o} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. $t_{\mbox{\tiny PLZ}}$ and $t_{\mbox{\tiny PHZ}}$ are the same as $t_{\mbox{\tiny dis}}.$
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms

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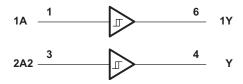
9 Detailed Description

9.1 Overview

NanoFree[™] package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

9.2 Functional Block Diagram



9.3 Feature Description

- 1.65 V to 5.5 V operating voltage range
- · Allows down voltage translation
 - 5 V to 3.3 V
 - 5 V or 3.3 V to 1.8 V
- Inputs accept voltages to 5.5 V
 - 5-V tolerance on input pin
- I_{off} feature
 - Allows voltage on the inputs and outputs when V_{CC} is 0 V
 - Able to reduce leakage when V_{CC} is 0 V
- Schmitt-Trigger Input can improve the noise immunity capability

9.4 Device Functional Modes

INPUT A	OUTPUT Y
Н	Н
L	L

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10 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The SN74LVC2G17 device contains two buffers and performs the Boolean function Y = A. The device functions as two independent buffers, but because of Schmitt action, it may have different input threshold levels for positive-going (V_{T+}) and negative-going (V_{T-}) signals.

10.2 Typical Power Button Circuit

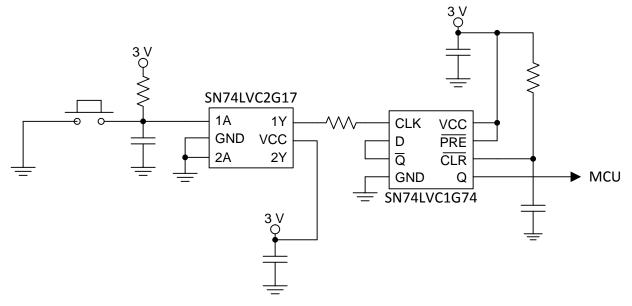


Figure 4. Device Power Button Circuit

10.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. Outputs can be combined to produce higher drive but the high drive will also create faster edges into light loads so routing and load conditions should be considered to prevent ringing.

10.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
 - For rise time and fall time specifications, see ($\Delta t/\Delta V$) in *Recommended Operating Conditions* table.
 - For specified high and low levels, see (V_{IH} and V_{II}) in Recommended Operating Conditions table.
 - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}.

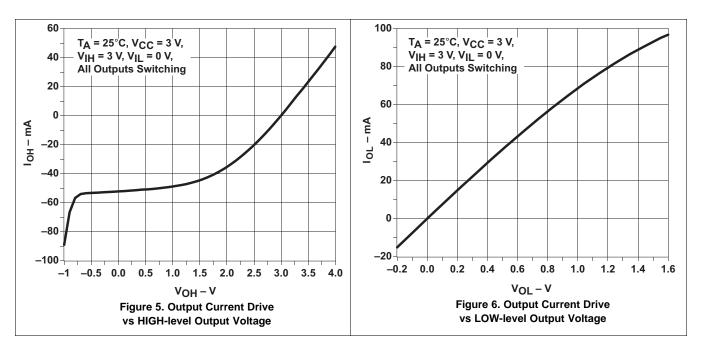
2. Recommend Output Conditions:

- Load currents should not exceed 50 mA per output and 100 mA total for the part.
- Series resistors on the output may be used if the user desires to slow the output edge signal or limit the output current.



Typical Power Button Circuit (continued)

10.2.3 Application Curves



11 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the *Recommended Operating Conditions* table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1 μ F capacitor is recommended. If there are multiple V_{CC} terminals then 0.01 μ F or 0.022 μ F capacitors are recommended for each power terminal. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. Multiple bypass capacitors may be paralleled to reject different frequencies of noise. The bypass capacitor should be installed as close to the power terminal as possible for the best results.

12 Layout

12.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Figure 7 are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} , whichever makes more sense or is more convenient.

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12.2 Layout Example



Figure 7. Layout Diagram

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13 Device and Documentation Support

13.1 Trademarks

NanoFree is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

13.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

13.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms and definitions.

14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.





4-Apr-2019

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
SN74LVC2G17DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	(6) CU NIPDAU CU SN	(3) Level-1-260C-UNLIM	-40 to 125	(4/5) (C175, C17F, C17K, C17R)	Samples
SN74LVC2G17DBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 125	(C175, C17F, C17K, C17R)	Samples
SN74LVC2G17DBVTG4	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C17F, C17R)	Samples
SN74LVC2G17DCK3	ACTIVE	SC70	DCK	6	3000	Pb-Free (RoHS)	CU SNBI	Level-1-260C-UNLIM	-40 to 85	(C7F, C7Z)	Samples
SN74LVC2G17DCKR	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 125	(C75, C7F, C7J, C7 K, C7R)	Samples
SN74LVC2G17DCKRE4	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C75	Samples
SN74LVC2G17DCKRG4	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C75	Samples
SN74LVC2G17DCKT	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 125	(C75, C7F, C7J, C7 K, C7R)	Samples
SN74LVC2G17DCKTE4	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C75	Samples
SN74LVC2G17DCKTG4	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C75	Samples
SN74LVC2G17DRYR	ACTIVE	SON	DRY	6	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C7	Samples
SN74LVC2G17DSF2	ACTIVE	SON	DSF	6	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C7	Samples
SN74LVC2G17DSFR	ACTIVE	SON	DSF	6	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C7	Samples
SN74LVC2G17YZPR	ACTIVE	DSBGA	YZP	6	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(C77, C7N)	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

PACKAGE OPTION ADDENDUM



4-Apr-2019

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74LVC2G17:

Automotive: SN74LVC2G17-Q1

■ Enhanced Product: SN74LVC2G17-EP

NOTE: Qualified Version Definitions:

- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product Supports Defense, Aerospace and Medical Applications

PACKAGE MATERIALS INFORMATION

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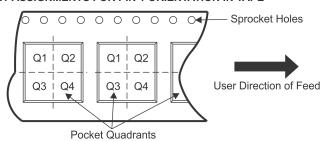
TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity AO

	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

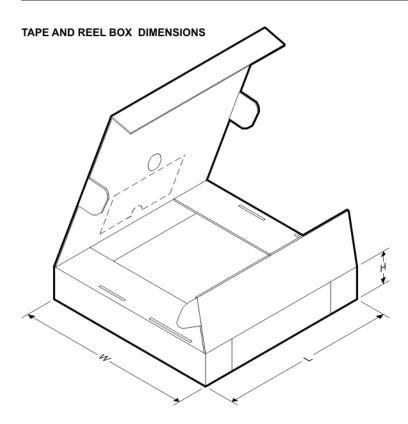


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G17DBVR	SOT-23	DBV	6	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC2G17DBVR	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC2G17DBVT	SOT-23	DBV	6	250	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC2G17DBVTG4	SOT-23	DBV	6	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC2G17DCKR	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC2G17DCKR	SC70	DCK	6	3000	180.0	9.2	2.3	2.55	1.2	4.0	8.0	Q3
SN74LVC2G17DCKR	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC2G17DCKR	SC70	DCK	6	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC2G17DCKRG4	SC70	DCK	6	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC2G17DCKT	SC70	DCK	6	250	180.0	9.2	2.3	2.55	1.2	4.0	8.0	Q3
SN74LVC2G17DCKT	SC70	DCK	6	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC2G17DCKT	SC70	DCK	6	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC2G17DCKTG4	SC70	DCK	6	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC2G17DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC2G17DSF2	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q3
SN74LVC2G17DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC2G17YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G17DBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
SN74LVC2G17DBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
SN74LVC2G17DBVT	SOT-23	DBV	6	250	180.0	180.0	18.0
SN74LVC2G17DBVTG4	SOT-23	DBV	6	250	180.0	180.0	18.0
SN74LVC2G17DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC2G17DCKR	SC70	DCK	6	3000	205.0	200.0	33.0
SN74LVC2G17DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC2G17DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC2G17DCKRG4	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC2G17DCKT	SC70	DCK	6	250	205.0	200.0	33.0
SN74LVC2G17DCKT	SC70	DCK	6	250	180.0	180.0	18.0
SN74LVC2G17DCKT	SC70	DCK	6	250	180.0	180.0	18.0
SN74LVC2G17DCKTG4	SC70	DCK	6	250	180.0	180.0	18.0
SN74LVC2G17DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC2G17DSF2	SON	DSF	6	5000	184.0	184.0	19.0
SN74LVC2G17DSFR	SON	DSF	6	5000	184.0	184.0	19.0
SN74LVC2G17YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.









NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.





NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).





NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation. 5. Refernce JEDEC MO-178.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



DCK (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AB.



DCK (R-PDSO-G6)

PLASTIC SMALL OUTLINE

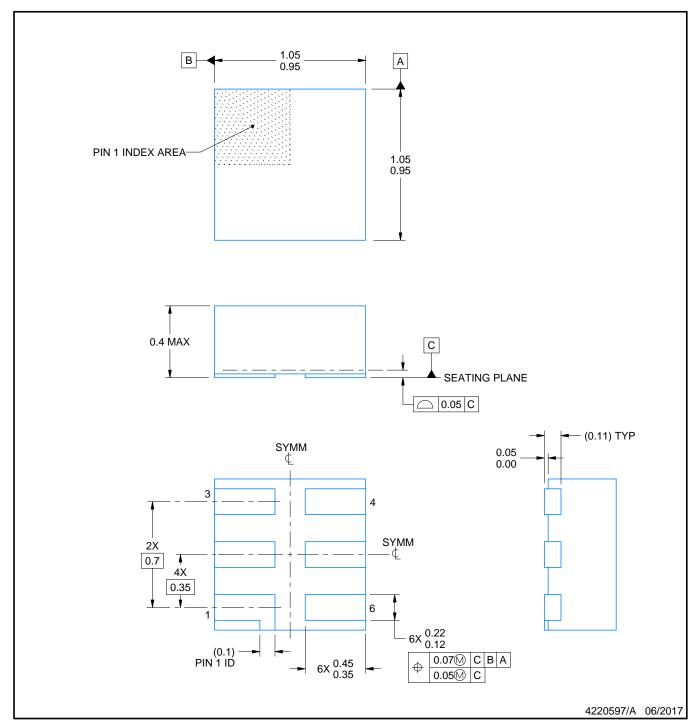


NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.







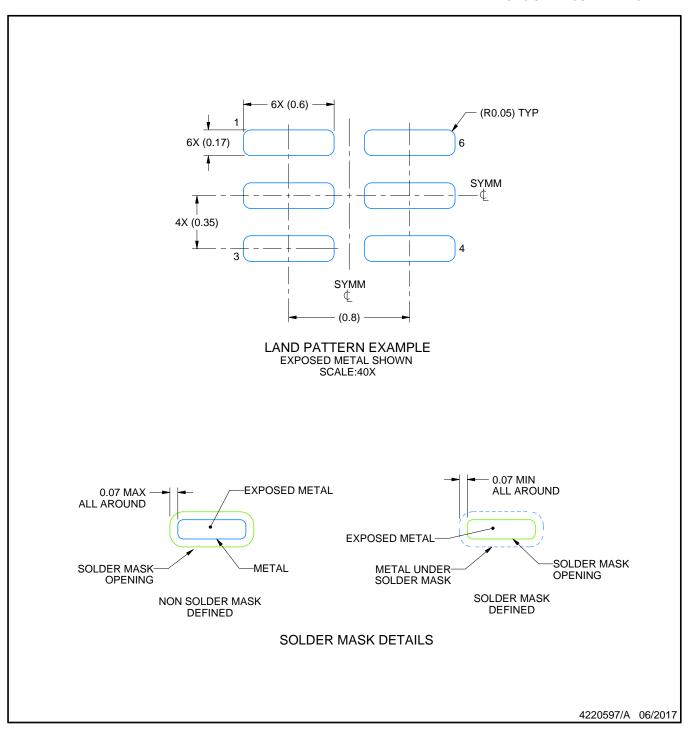
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.

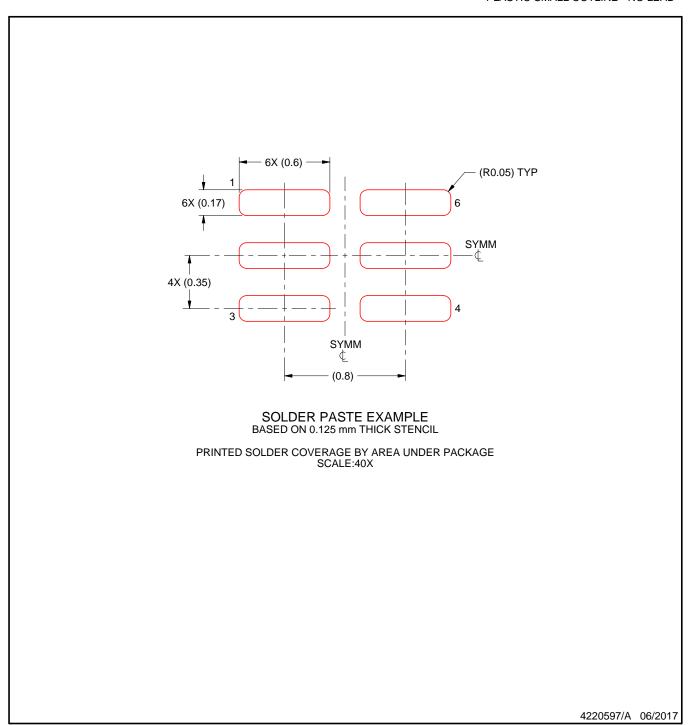




NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).





4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





DIE SIZE BALL GRID ARRAY



NOTES:

NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. NanoFree[™] package configuration.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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